

REMARKS

In the Office Action, the Examiner rejects Claims 4-6 under 35 USC §112, second paragraph, as being indefinite, and under 35 USC §101. In order to advance the prosecution of this application, Applicant has canceled Claims 4-6, rendering these rejections moot.

The Examiner further rejects Claims 12-43 under 35 USC §102(e) as being unpatentable over Yamazaki et al. '758. This rejection is respectfully traversed.¹

The claims of the present application are directed to an organic electroluminescence display device. As explained below, Yamazaki does not disclose or suggest the structure of the claimed invention.

Claims 12-14, 18-20, 24-26 and 30-32 all specifically recite “an insulating film comprising a nitride *on* the resin substrate.” (emphasis added) The Examiner alleges that Yamazaki discloses an insulating film 104 comprising a nitride on the resin substrate. Yamazaki, however, discloses an insulating layer 104, which may be made of silicon nitride, on a resin layer 102, and the resin layer 102 is on the substrate 101 (see Fig. 1A and 1B; cols. 3-4). Hence, the insulating layer in Yamazaki is over, not on the substrate.

Further, with regard to Claims 18-20, 24-26 and 30-32, Yamazaki does not disclose or suggest a thin film transistor formed over the insulating film comprising a nitride, as required in the claims. Instead, Yamazaki teaches that the insulating film 104 is a gate insulating film which is a part of the thin film transistor.

Additionally, with regard to Claims 30-32, Yamazaki does not disclose or suggest an insulating film comprising a nitride on the resin substrate and a channel region comprising

¹ The amendment made to Claim 36 is merely to correct a typographical error in the claim and is not a narrowing amendment.

crystalline silicon formed over the insulating film, as required in the claims. Instead, Yamazaki discloses a crystalline silicon film over the resin substrate and an insulating film comprising a nitride over the crystalline silicon film.

Therefore, Yamazaki does not disclose or suggest the structure of the device claimed in Claims 12-14, 18-20, 24-26 and 30-32.

Claims 15-17, 21-23, 27-29 and 33-35 all specifically recite “an underlying insulating film formed *on* the resin substrate; wherein the underlying insulating film comprises a first insulating film comprising a nitride and a second insulating film comprising silicon oxide.” (emphasis added). Hence, each of these claims require a nitride insulating film on the resin substrate. As explained above, Yamazaki discloses that the insulating layer of nitride is on a resin layer and is over, not on the substrate.

Further, with regard to Claims 21-23, 27-29 and 33-35, Yamazaki does not disclose or suggest a thin film transistor formed over the insulating film comprising a nitride, as required in the claims. Instead, Yamazaki teaches that the insulating film 104 is a gate insulating film which is a part of the thin film transistor.

Further, as explained above, Claims 21-23, 27-29 and 33-35 recite “an underlying insulating film formed on the resin substrate; wherein the underlying insulating film comprises a first insulating film comprising a nitride and a second insulating film comprising silicon oxide” and “a thin film transistor formed over the insulating layer.” Yamazaki does not disclose or suggest a display device with both of these features.

Additionally, with regard to Claims 33-35, Yamazaki does not disclose or suggest an insulating film comprising a nitride on the resin substrate and a channel region comprising crystalline silicon formed over the insulating film, as required in the claims. Instead, Yamazaki

discloses a crystalline silicon film over the resin substrate and an insulating film comprising a nitride over the crystalline silicon film.

Therefore, Yamazaki does not disclose or suggest the structure of the device claimed in Claims 15-17, 21-23, 27-29 and 33-35.

Claims 36-43 all specifically recite “an insulating film comprising an oxy-nitride *on* the resin substrate.” (emphasis added). As explained above, Yamazaki discloses that the insulating layer of nitride is on a resin layer and is over, not on the substrate.

Further, each of Claims 36-43 require that the insulating film comprises an oxy-nitride. While the Examiner alleges, but does not specify where, that Yamazaki discloses an insulating film of silicon oxy-nitride, Applicant and the undersigned have reviewed the reference, both manually and electronically, and could find no reference to silicon oxy-nitride or oxy-nitride. Instead, Yamazaki states that the gate-insulating film 104 may be made from silicon nitride instead of silicon oxide. See e.g. col.4, lns. 5-6.

Furthermore, with regard to Claims 38-43, Yamazaki does not disclose or suggest a thin film transistor formed over the insulating film comprising a nitride, as required in the claims. Instead, Yamazaki teaches that the insulating film 104 is a gate insulating film which is a part of the thin film transistor.

Additionally, with regard to Claims 42-43, Yamazaki does not disclose or suggest an insulating film comprising a nitride on the resin substrate and a channel region comprising crystalline silicon formed over the insulating film, as required in the claims. Instead, Yamazaki discloses a crystalline silicon film over the resin substrate and an insulating film comprising a nitride over the crystalline silicon film.

Therefore, Yamazaki does not disclose or suggest the structure of the device claimed in Claims 36-43.

Accordingly, since Yamazaki does not disclose or suggest the claimed invention, the claims are patentable thereover, and it is respectfully requested that the rejection be withdrawn.

In the Office Action Summary, the Examiner states that none of the certified copies of the priority documents have been received. However, as stated in the transmittal form for this application, the certified copy of the priority document for serial no.10-333853 filed on November 25, 1998 in Japan was filed in parent U.S. application Serial No. 09/449,140. Acknowledgment of this filing is requested.

Please charge Deposit Account No. 50-1039 for any fee due for this amendment.

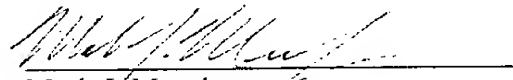
The application is now in a condition for allowance, and it is respectfully requested that it be allowed.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

Date:

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Marked-up copy of the claims as amended:

IN THE CLAIMS:

Please amend the claims as follows:

Cancel Claims 4-6.

36 (Amended). An organic electroluminescence display device comprising:

a resin substrate; and

an insulating film comprising an oxy-nitride on the resin substrate.